

## **Application Data Sheet**

### **Application Information**

Application Type::	Regular
Subject Matter::	Utility
Suggested Group Art Unit::	N/A
CD-ROM or CD-R?::	None
Sequence submission?::	None
Computer Readable Form (CRF)?::	No
Title::	SEMICONDUCTOR DEVICE INCLUDING TRANSISTOR WITH COMPOSITE GATE STRUCTURE AND TRANSISTOR WITH SINGLE GATE STRUCTURE, AND METHOD FOR MANUFACTURING THE SAME
Attorney Docket Number::	20433-00601-US2
Request for Early Publication?::	No
Request for Non-Publication?::	No
Total Drawing Sheets::	4
Small Entity?::	No
Petition included?::	No
Secrecy Order in Parent Appl.?::	No

### **Applicant Information**

Applicant Authority Type::	Inventor
Primary Citizenship Country::	Japan
Status::	Full Capacity
Given Name::	Katsuki
Family Name::	Hazama
City of Residence::	Tokyo
Country of Residence::	Japan

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6-3, Ohtemachi 2-chome, Chiyoda-ku  
City of mailing address:: Tokyo  
Country of mailing address:: Japan  
Postal or Zip Code of mailing address:: 100-8071

**Correspondence Information**

Correspondence Customer Number:: 30678

**Representative Information**

Representative Customer Number:: 30678

**Domestic Priority Information**

Application::	Continuity Type::	Parent Application::	Parent Filing Date::
This Application	Continuation of	10/118,039	04/09/2002
Which is a	Divisional of	09/706,810	11/07/2000

**Foreign Priority Information**

Country::	Application number::	Filing Date::	Priority Claimed::
Japan	07-276292	09/29/95	Yes

**Assignee Information**

Assignee name:: Nippon Steel Corporation  
6-3, Ohtemachi 2-chome  
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